

MITSUBISHI HIGH SPEED CMOS
M74HC08P/FP/DP

QUADRUPLE 2-INPUT POSITIVE AND GATE

DESCRIPTION

The M74HC08 is a semiconductor integrated circuit consisting of four 2-input positive-logic AND gates, usable as negative-logic OR gates.

FEATURES

- High-speed: 9.5ns typ. ($C_L=15\text{pF}$, $V_{CC}=5\text{V}$)
- Low power dissipation: $5\mu\text{W}/\text{package}$, max ($V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$, quiescent state)
- High noise margin: 30% of V_{CC} , min ($V_{CC}=4.5\text{V}$, 6V)
- Capable of driving 10 74LSTTL loads
- Wide operating voltage range: $V_{CC}=2\sim 6\text{V}$
- Wide operating temperature range: $T_a=-40\sim+85^\circ\text{C}$

APPLICATION

General purpose, for use in industrial and consumer digital equipment.

FUNCTIONAL DESCRIPTION

Use of silicon gate technology allows the M74HC08 to maintain the low power dissipation and high noise margin characteristics of the standard CMOS logic 4000B series while giving high-speed performance equivalent to the 74LS08.

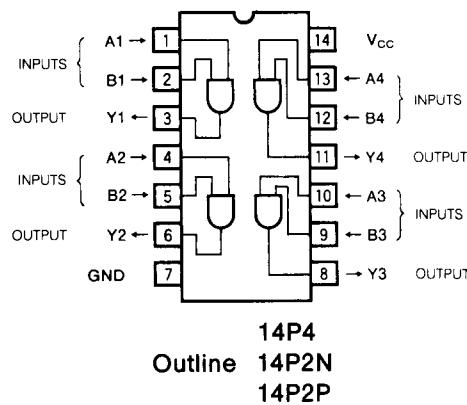
Buffered outputs Y improve input-to-output transfer characteristics and minimizes output impedance variations with respect to input voltage variations.

When both inputs A and B are high, the output Y will become high, and when at least one of the inputs is low, Y will become low.

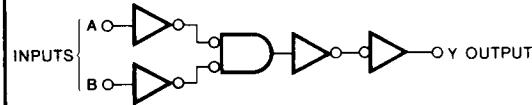
FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	L
H	L	L
L	H	L
H	H	H

PIN CONFIGURATION (TOP VIEW)



LOGIC DIAGRAM (EACH GATE)



ABSOLUTE MAXIMUM RATINGS ($T_a = -40\sim+85^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		$-0.5\sim+7.0$	V
V_I	Input voltage		$-0.5\sim V_{CC}+0.5$	V
V_O	Output voltage		$-0.5\sim V_{CC}+0.5$	V
I_{IK}	Input protection diode current	$V_I < 0\text{V}$	-20	mA
		$V_I > V_{CC}$	20	
I_{OK}	Output parasitic diode current	$V_O < 0\text{V}$	-20	mA
		$V_O > V_{CC}$	20	
I_O	Output current per output pin		± 25	mA
I_{CC}	Supply/GND current	V_{CC}, GND	± 50	mA
P_d	Power dissipation	(Note 1)	500	mW
T_{stg}	Storage temperature range		$-65\sim+150$	°C

Note 1 : M74HC08FP, $T_a = -40\sim+60^\circ\text{C}$ and $T_a = 60\sim85^\circ\text{C}$ are derated at $-6\text{mW}/^\circ\text{C}$.
M74HC08DP, $T_a = -40\sim+50^\circ\text{C}$ and $T_a = 50\sim85^\circ\text{C}$ are derated at $-5\text{mW}/^\circ\text{C}$.

QUADRUPLE 2-INPUT POSITIVE AND GATE

RECOMMENDED OPERATING CONDITIONS ($T_a = -40 \sim +85^\circ\text{C}$)

Symbol	Parameter	Limits			Unit
		Min	Typ	Max	
V_{CC}	Supply voltage	2		6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_{opr}	Operating temperature range	-40		+85	$^\circ\text{C}$
t_r, t_f	Input risetime, falltime	$V_{CC} = 2.0\text{V}$	0	1000	ns
		$V_{CC} = 4.5\text{V}$	0	500	
		$V_{CC} = 6.0\text{V}$	0	400	

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits					Unit	
			$V_{CC}(\text{V})$	25°C			-40~+85°C		
				Min	Typ	Max	Min	Max	
V_{IH}	High-level input voltage	$V_O = 0.1\text{V}, V_{CC} = 0.1\text{V}$ $ I_O = 20\mu\text{A}$	2.0	1.5			1.5		V
			4.5	3.15			3.15		
			6.0	4.2			4.2		
V_{IL}	Low-level input voltage	$V_O = 0.1\text{V}$ $ I_O = 20\mu\text{A}$	2.0			0.5		0.5	V
			4.5			1.35		1.35	
			6.0			1.8		1.8	
V_{OH}	High-level output voltage	$V_I = V_{IH}$	$I_{OH} = -20\mu\text{A}$	2.0	1.9		1.9		V
			$I_{OH} = -20\mu\text{A}$	4.5	4.4		4.4		
			$I_{OH} = -20\mu\text{A}$	6.0	5.9		5.9		
			$I_{OH} = -4.0\text{mA}$	4.5	4.18		4.13		
			$I_{OH} = -5.2\text{mA}$	6.0	5.68		5.63		
V_{OL}	Low-level output voltage	$V_I = V_{IH}, V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0		0.1	0.1		V
			$I_{OL} = 20\mu\text{A}$	4.5		0.1	0.1		
			$I_{OL} = 20\mu\text{A}$	6.0		0.1	0.1		
			$I_{OL} = 4.0\text{mA}$	4.5		0.26	0.33		
			$I_{OL} = 5.2\text{mA}$	6.0		0.26	0.33		
I_{IH}	High-level input current	$V_I = 6\text{V}$		6.0		0.1	1.0	μA	
I_{IL}	Low-level input current	$V_I = 0\text{V}$		6.0		-0.1	-1.0	μA	
I_{CC}	Quiescent supply current	$V_I = V_{CC}, \text{GND}, I_O = 0\mu\text{A}$		6.0		1.0	10.0	μA	

QUADRUPLE 2-INPUT POSITIVE AND GATE

SWITCHING CHARACTERISTICS ($V_{CC} = 5V$, $T_a = 25^\circ C$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t_{TLH}	Low-level to high-level and high-level to low-level output transition time				10	ns
t_{THL}	Output transition time				10	ns
t_{PLH}	Low-level to high-level and high-level to low-level output propagation time	$C_L = 15pF$ (Note 3)			15	ns
t_{PHL}	Output propagation time				20	ns

SWITCHING CHARACTERISTICS ($V_{CC} = 2\sim 6V$, $T_a = -40\sim +85^\circ C$)

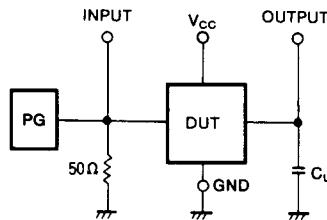
Symbol	Parameter	Test conditions	Limits					Unit
			25°C			-40~+85°C		
			$V_{CC}(V)$	Min	Typ	Max	Min	Max
t_{TLH}	Low-level to high-level and high-level to low-level output transition time		2.0			75		95
			4.5			15		19
			6.0			13		16
t_{THL}	Output transition time	$C_L = 50pF$ (Note 3)	2.0			75		95
			4.5			15		19
			6.0			13		16
t_{PLH}	Low-level to high-level and high-level to low-level output propagation time		2.0			121		151
			4.5			24		30
			6.0			20		25
t_{PHL}	Output propagation time		2.0			121		151
			4.5			24		30
			6.0			20		25
C_I	Input capacitance					10		10
C_{PD}	Power dissipation capacitance (Note 2)				40			pF

Note 2 : C_{PD} is the internal capacitance of the IC calculated from operation supply current under no-load conditions. (per gate)

The power dissipation during operation under no-load conditions is calculated using the following formula:

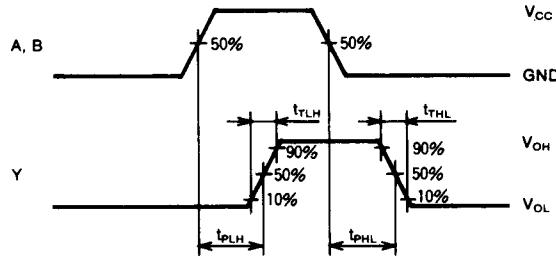
$$P_D = C_{PD} \cdot V_{CC}^2 \cdot f_t + I_{CC} \cdot V_{CC}$$

Note 3 : Test Circuit



- (1) The pulse generator (PG) has the following characteristics (10%~90%): $t_r = 6ns$, $t_f = 6ns$
- (2) The capacitance C_L includes stray wiring capacitance and the probe input capacitance.

TIMING DIAGRAM



**MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES**

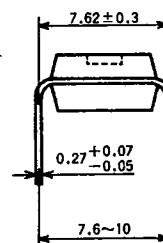
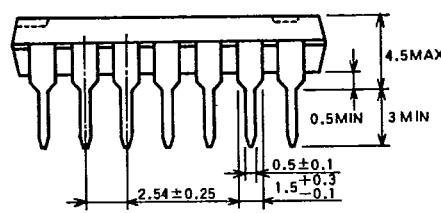
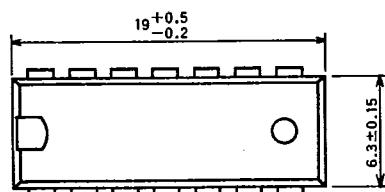
6249827 MITSUBISHI {DGTL LOGIC}

91D 12849

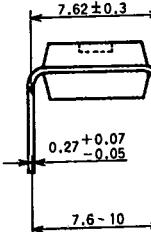
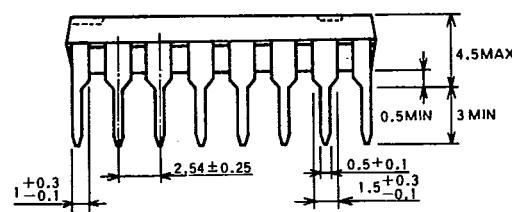
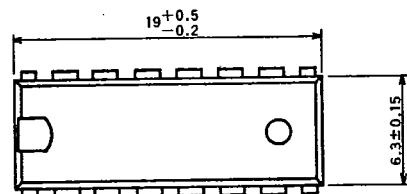
D T-90-20

TYPE 14P4 14-PIN MOLDED PLASTIC DIP

Dimension in mm

**TYPE 16P4 16-PIN MOLDED PLASTIC DIP**

Dimension in mm

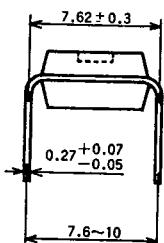
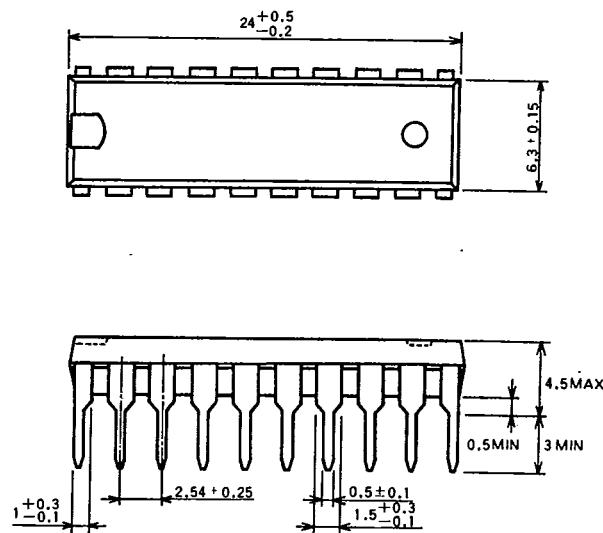


MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

91D 12850 D T-90-20

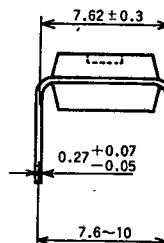
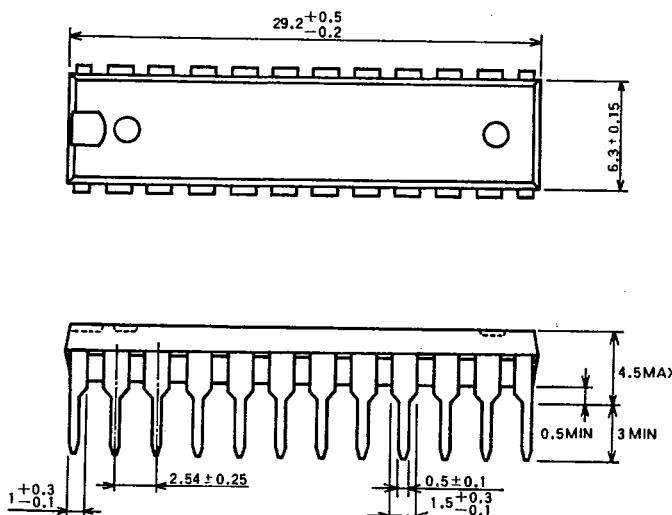
TYPE 20P4 20-PIN MOLDED PLASTIC DIP

Dimension in mm



TYPE 24P4D 24-PIN MOLDED PLASTIC DIP

Dimension in mm



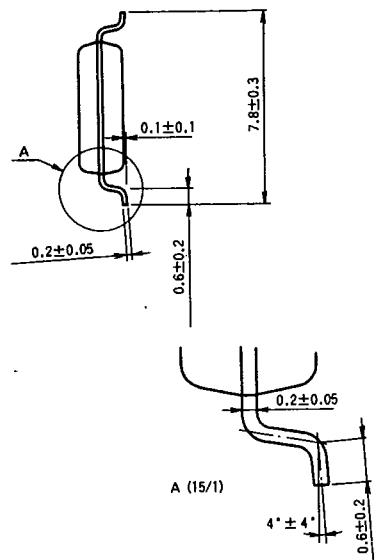
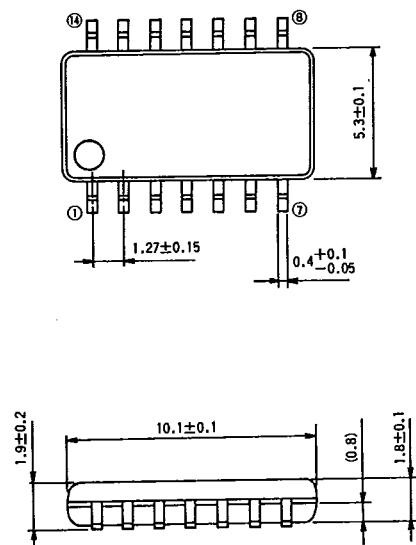
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PACKAGE OUTLINES

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91D 12851 D T-90.20

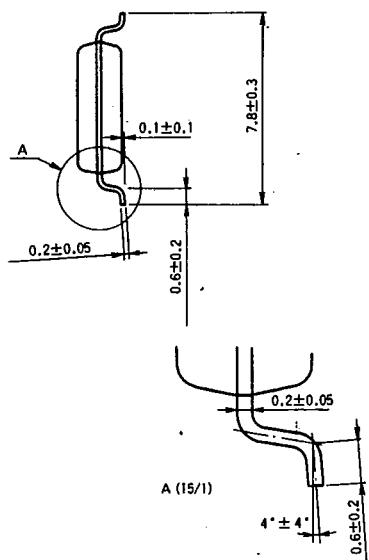
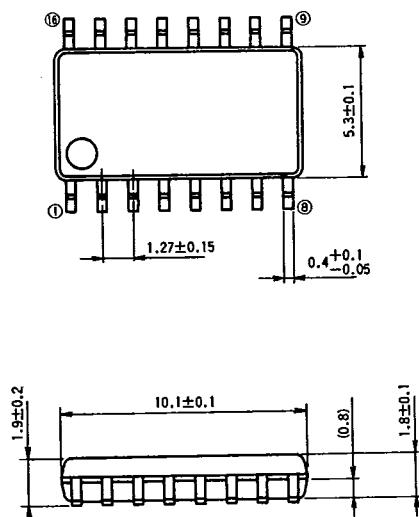
TYPE 14P2N 14PIN MOLDED PLASTIC SOP

Dimension in mm



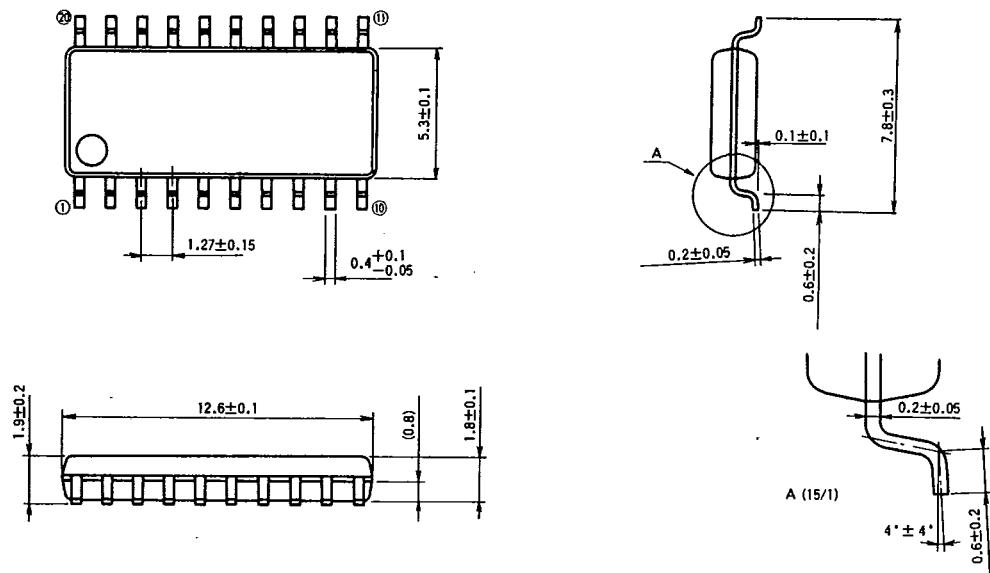
TYPE 16P2N 16PIN MOLDED PLASTIC SOP

Dimension in mm



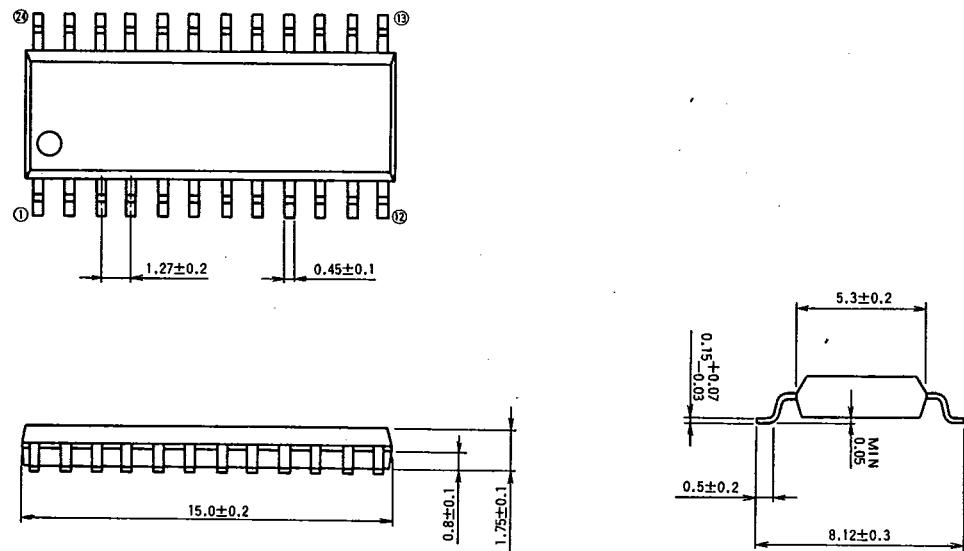
TYPE 20P2N 20PIN MOLDED PLASTIC SOP

Dimension in mm



TYPE 24P2 24PIN MOLDED PLASTIC SOP

Dimension in mm

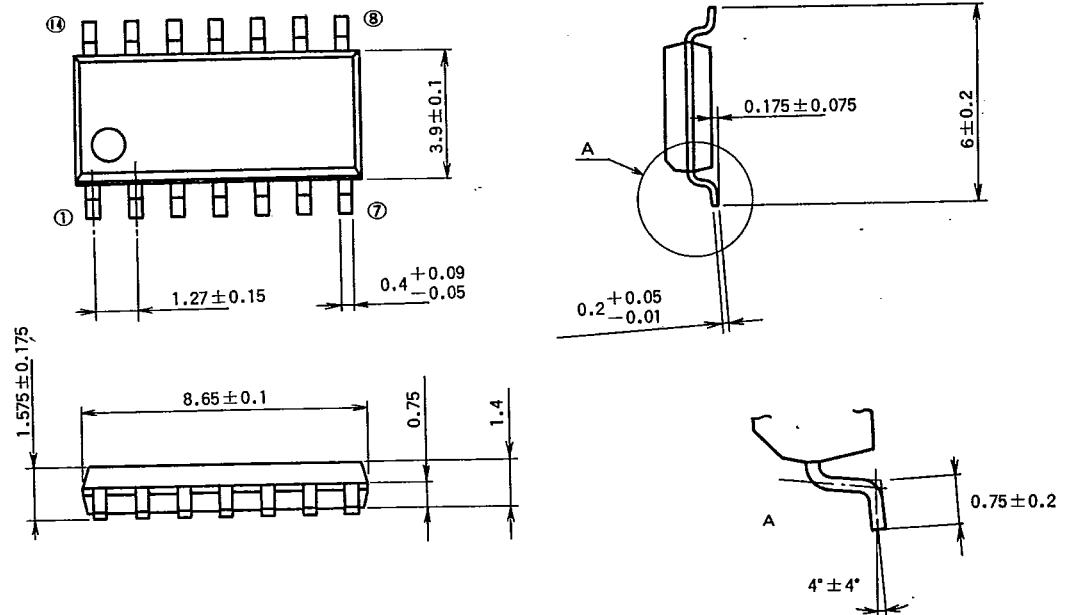


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91D 12853 D T90-20

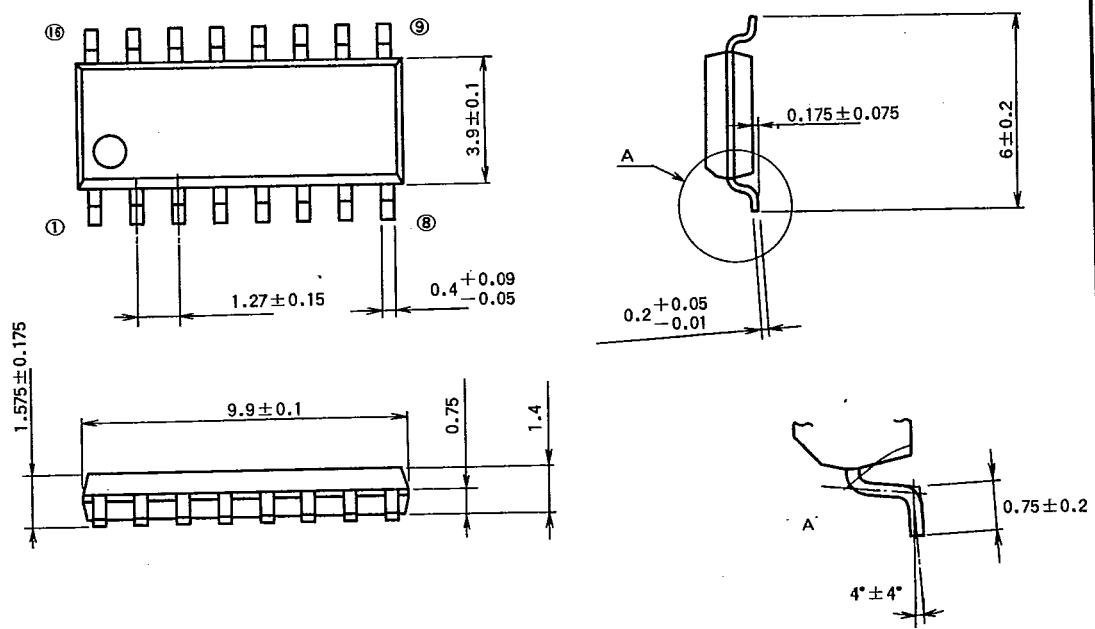
TYPE 14P2P 14-PIN MOLDED PLASTIC SOP(JEDEC 150mil body)

Dimension in mm



TYPE 16P2P 16-PIN MOLDED PLASTIC SOP(JEDEC 150mil body)

Dimension in mm



PACKAGE OUTLINES

6249827 MITSUBISHI (DGTL LOGIC)

91D 12854 D T-90-20

TYPE 20P2V 20-PIN MOLDED PLASTIC SOP(JEDEC 300mil body)

